## K. Memory (Design & Process Technology) 분과 [FG2-K] Devices for Neuromorphic Computing II

FG2-K-1 10:45~11:15	[초청] Neural Networks with Memristor Crossbar Network YeonJoo Jeong KIST
FG2-K-2 11:15~11:30	Performance Improvement of InGaZnO-based RRAM with Al <sub>2</sub> O <sub>3</sub> Inserting Tunneling Barrier Layer Jingyu Park, Jun Tae Jang, Geumho Ahn, Jungi Min, Sung-Jin Choi, Dong Myong Kim, and Dae Hawn Kim <sup>1</sup> School of Electrical Engineering, Kookmin University
FG2-K-3 11:30~11:45	Multilevel Resistive Switching Characteristics in Bioinspired Solid Polymer Electrolyte Chitosan-based Memristors Shin-yi Min and Won-Ju Cho Department of Electronic Materials Engineering, Kwangwoon University
FG2-K-4 11:45~12:00	Variation Effect on Stateful Logic Gates and Practical Memristive System Young Seok Kim, Myeong Won Son, Hanchan Song, Juseong Park, Jangho An, Jae Bum Jeon, Geun Young Kim, Seoil Son, and Kyung Min Kim Department of Materials Science and Engineering, KAIST
FG2-K-5 12:00~12:15	Introduction of New APBM Stateful Logics based on Two Antiparallel Bipolar Memristors  Nuo Xu <sup>1,2</sup> , Tae Gyun Park <sup>2</sup> , Hae Jin Kim <sup>2</sup> , Xinglong Shao <sup>2</sup> , Kyung Jean Yoon <sup>2</sup> , Tae Hyung Park <sup>2</sup> , Liang Fang <sup>1</sup> , Kyung Min Kim <sup>3</sup> , and Cheol Seong Hwang <sup>2</sup> <sup>1</sup> National University of Defense Technology, <sup>2</sup> Seoul National University, <sup>3</sup> KAIST